

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.003C1	APPLICATION NO. 09/037,945
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Pierre C. Fazan et al.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE March 10, 1998	GROUP Unknown <b>2814</b>

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
G	4,109,030	8/78	Briska et al.	—	—	
G	4,624,046	11/86	Shideler et al.	—	—	
G	5,470,783	11/95	Chin et al.	—	—	
G	5,502,09	03/96	Lin	—	—	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
G	1	"Extended Abstracts of the Electrochemical Society Meeting", Fall 1993, pp. 281-282
G	2	<b>Sze, S.M.</b> "High-Pressure Oxidation", <i>VLSI Technology</i> , 2d Edition, McGraw-Hill, Inc., New York, 1988, pp. 121-123
G	3	Wolf, Stanley, "Isolation Technologies for Integrated Circuits", <i>Silicon Processing for the VLSI Era Vol. 2: Process Integration</i> , Lattice Press, Sunset Beach, CA, 1990, pp. 17-27
G	4	Marshall, S. Et al., "Dry Pressure Local Oxidation of Silicon for IC Isolation", <i>Journal of the Electrochemical Society</i> (Oct. 1975), Vol. 122, No. 19, pp. 1411-1412

EXAMINER <b>Fourson</b>	DATE CONSIDERED <b>5/4/99</b>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	